

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S32	185	(phase adj change) with capacitor	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/09/09 13:18
S33	1482	(phase adj change) with memory	US-PGPU B; USPAT; EPO; JPO	OR	ON	2004/11/24 14:16
S35	1661	S32 or S33	US-PGPU B; USPAT; EPO; JPO	OR	ON	2004/11/24 14:16
S36	1661	S35 and (phase adj change capacitor memory)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2004/11/24 14:23
S37	416	"22" and ((phase adj change) with electrode)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2004/11/24 14:19
S38	182	S36 and ((phase adj change) with electrode)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2004/11/24 14:19
S39	121	S38 and ((recess trench hole via groove opening) with electrode)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2004/11/24 14:21
S40	131	S38 and ((recess trench hole via groove opening pore damascene) with electrode)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/09/09 13:23
S41	2081	438/259,270.ccls.	US-PGPU B; USPAT; EPO; JPO	OR	ON	2004/11/24 14:22
S42	0	S41 and S36	US-PGPU B; USPAT; EPO; JPO	OR	ON	2004/11/24 14:22

S43	592	S41 and (phase adj change capacitor memory)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2004/11/24 14:23
S44	246	S43 and ((recess trench hole via groove opening pore damascene) with electrode)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2004/11/24 14:58
S45	2	S43 and (phase adj change)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2004/11/24 14:59
S46	0	S41 and ((phase adj change) with (memory capaitor material layer))	US-PGPU B; USPAT; EPO; JPO	OR	ON	2004/11/24 15:00
S47	10493	((phase adj change) with (memory capaitor material layer))	US-PGPU B; USPAT; EPO; JPO	OR	ON	2004/11/24 15:01
S48	40	((phase adj change) with (memory capaitor material layer)) with (electrode near5 (recess trench pore damascene hole opening groove aperture))	US-PGPU B; USPAT; EPO; JPO	OR	ON	2004/11/24 15:03
S49	2161	(phase adj change) with (capacitor memory)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/09/09 13:18
S50	3110	(phase near3 change) with (capacitor memory)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/09/09 13:19
S51	3869	(phase near3 change\$3 chalcogenide ovonic) with (capacitor memory)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/09/09 13:24
S52	433445	(recess trench hole via groove opening pore damascene) with (electrode plug pillar column)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/09/09 13:28

S53	4213	(phase near3 change\$3 chalcogenide ovonic) with (recess trench hole via groove opening pore damascene)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/09/09 13:25
S54	1960	(phase near3 change\$3 chalcogenide ovonic) near5 (recess trench hole via groove opening pore damascene)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/09/09 13:26
S55	424	S51 and (phase near3 change\$3 chalcogenide ovonic) near5 (recess trench hole via groove opening pore damascene)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/09/09 13:28
S56	279	S55 and S52	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/09/09 13:27
S57	279	S56 and (phase near3 change\$3 chalcogenide ovonic recess trench hole via groove opening pore damascene)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/09/09 13:28
S58	279	S57 and (recess trench hole via groove opening pore damascene electrode plug pillar column)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/09/12 08:22
S59	49273	chen.inv.	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/09/12 08:23
S60	158	chenn ear2 bomy.inv.	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/09/12 08:23
S61	77	chen near2 bomy.inv.	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/09/12 08:23

